

HIR Package Reliability Roadmap and Co-packaged Optics

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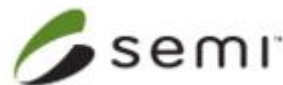
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Richard Rao (Marvell Corporation), Shubhada Sahasrabudhe (Intel)



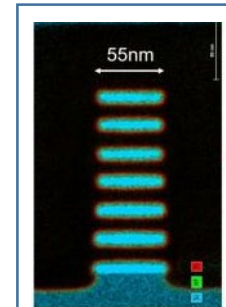
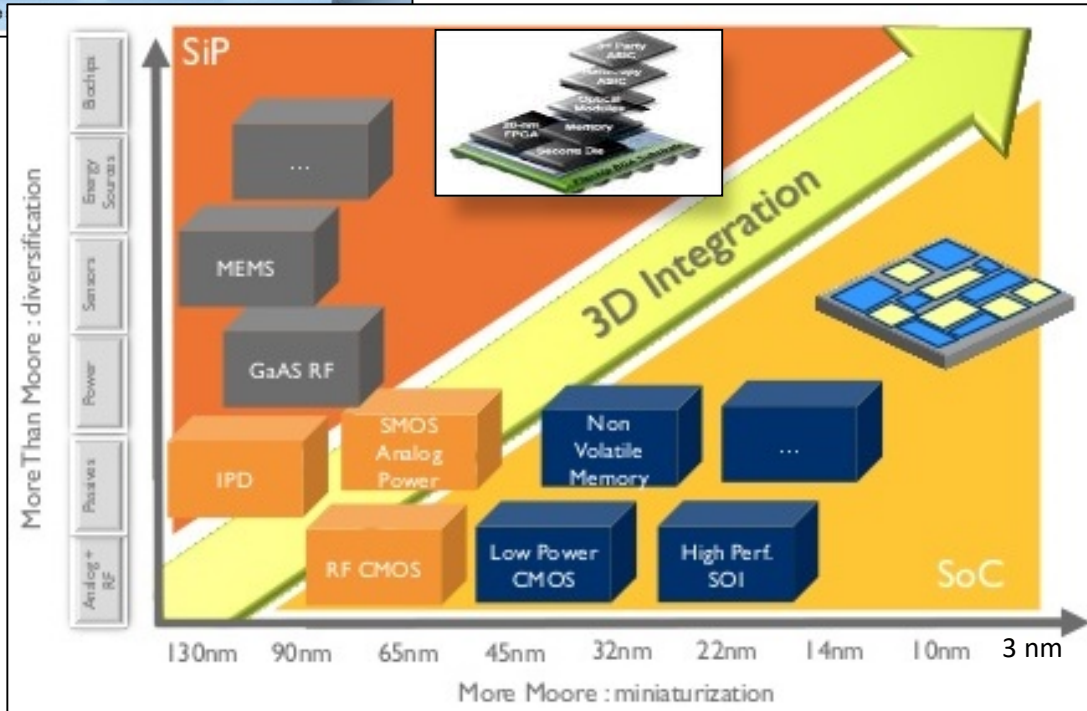
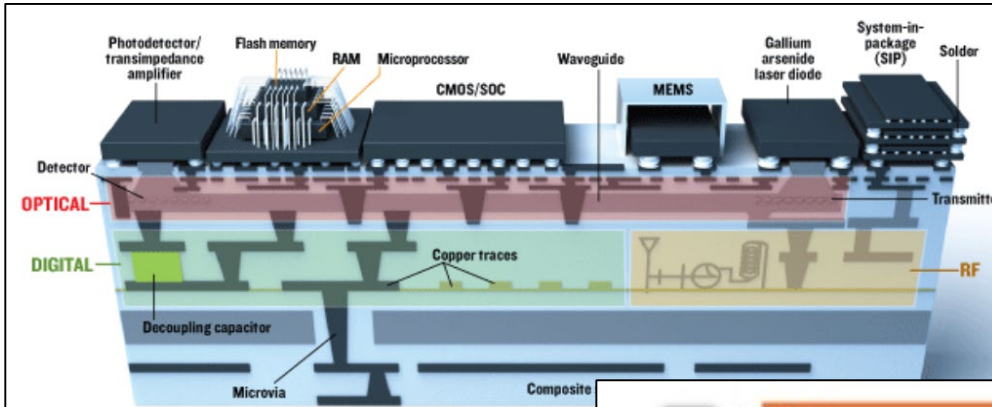
Heterogeneous Integration: SysMoore ('More than Moore')



HETEROGENEOUS INTEGRATION ROADMAP

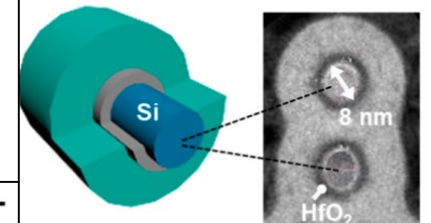
Convergence of Semiconductor and Packaging Technologies

Source: Yole 2.5D/3D Business Update 2015

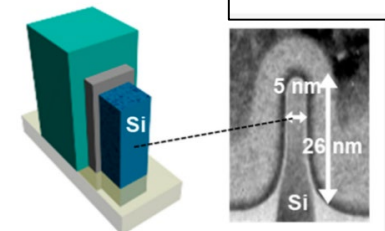


GAA Nanosheet

GAA NW-FET

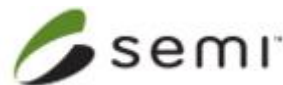
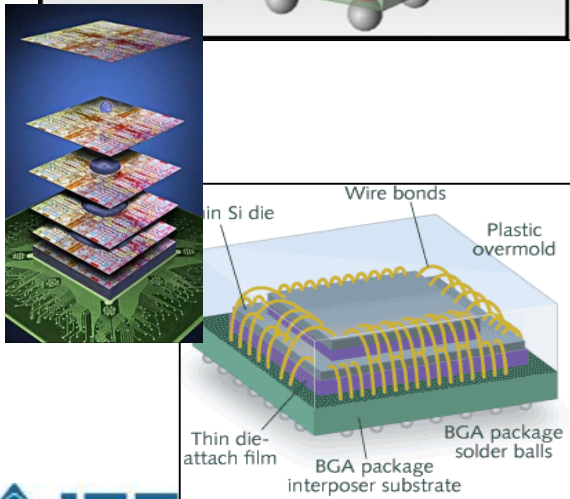
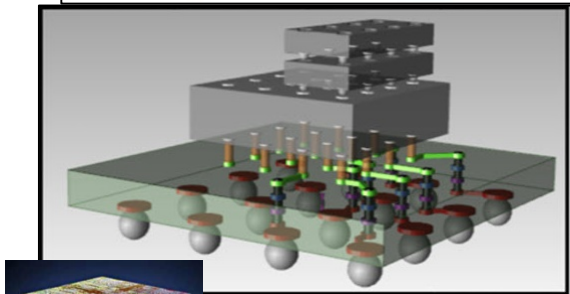


FinFET



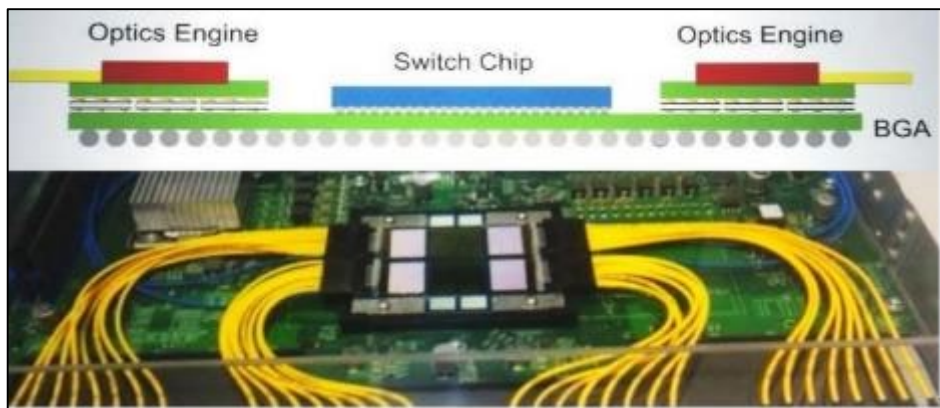
Multi-physics

Multi-scale



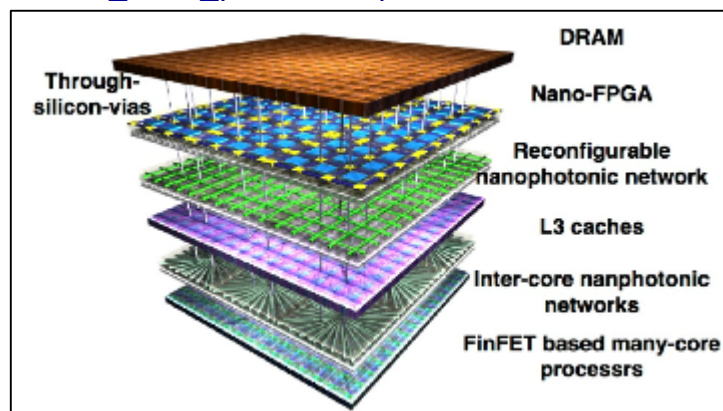
Heterogenous integration

- ❑ Electronic (Passive/Active)/Photonic/MEMS/Sensor devices
- ❑ Digital; Analog; Logic; Memory; Power; RF
- ❑ System, Package (Chipselets) and Wafer levels, including Interconnects and Substrates
- ❑ 2.5D and 3D Packaging technologies



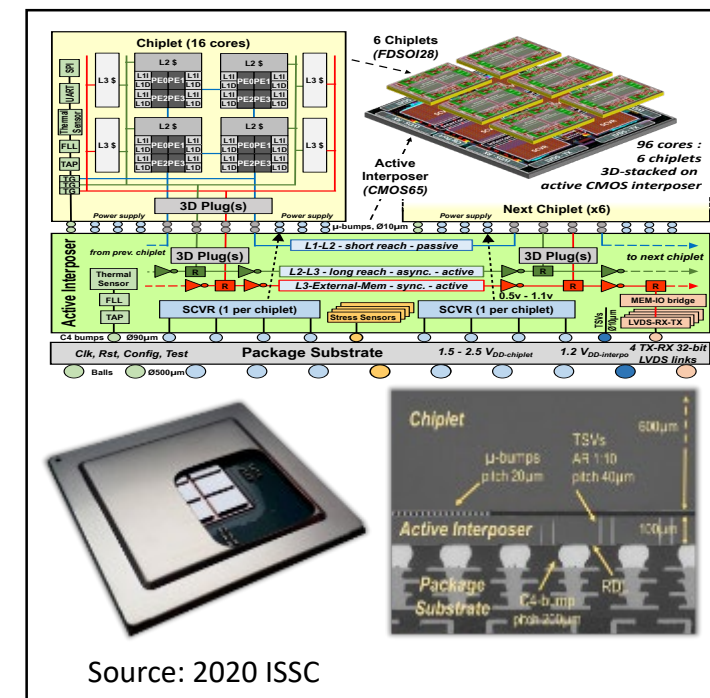
Photonic switching devices and SIP concepts

https://eps.ieee.org/images/files/HIR_2019/HIR1_ch09_photonics.pdf



Photonics applications:

5G, IoT, Data Centers, Automotive (LIDAR), Aerospace and Defense



Source: 2020 ISSC

HIR Technical Working Groups

3-8-2018

HI for Market Applications

- Mobile
- IoT
- Medical, Health & Wearables
- Automotive
- High Performance Computing & Data Center
- Aerospace & Defense

Heterogeneous Integration Components

- Single Chip and Multi Chip Packaging (including Substrates)
- Integrated Photonics
- Integrated Power Electronics
- MEMS & Sensor integration
- RF and Analog Mixed Signal

Cross Cutting topics

- Materials & Emerging Research Materials
- Emerging Research Devices
- Interconnect
- Test
- Supply Chain
- Security
- Thermal Management

Integration Processes

- SiP
- 3D +2.5D
- WLP (fan in and fan out)

Design & Reliability

- Co-Design
- Modeling and Simulation
- Reliability

Reliability is a cross-cutting TWG: Cross-TWG interactions

	Reliability Targets	Life Cycle Conditions	Design for Reliability	Manufacturing for Reliability	Qualification for Reliability	Sustaining for Reliability	Supply Chain	Life Cycle Economics & Cost
Applications	Mobile; IoT; MHW; Automotive; HPC; Aerospace		Electromigration; Materials; Co-Design and Simulation; SCMCI; WLP; 2.5D/3D; Interconnects; SIP; Photonics; MEMS/Sensors; Power; RF/Analog; Test	Mobile; IoT; MHW; Automotive; HPC; Aerospace	Mobile; IoT; MHW; Automotive; HPC; Aerospace	Mobile; IoT; MHW; Automotive; HPC; Aerospace	Supply Chain TWG	No TWGs yet ??
Package Integration		WLP; 2.5D/3D; Interconnects; SIP; SCMCI; Test		WLP; 2.5D/3D; Interconnects; SIP; SCMCI	WLP; 2.5D/3D; Interconnects; SIP; SCMCI; Security			
SiP Technologies		Photonics; MEMS/Sensors; Power; RF/Analog; Test		Photonics; MEMS/Sensors; Power; RF/Analog; Test	Photonics; MEMS/Sensors; Power; RF/Analog; Security			

Integrated photonics: Challenges & solutions

https://eps.ieee.org/images/files/HIR_2019/HIR1_ch09_photonics.pdf

Difficult Challenges

- Physical density of bandwidth
- Thermal management
- Test access for SiP, 3D & Heterogeneous integration
- Photonic Switching to the package
- Cost

Potential Solutions

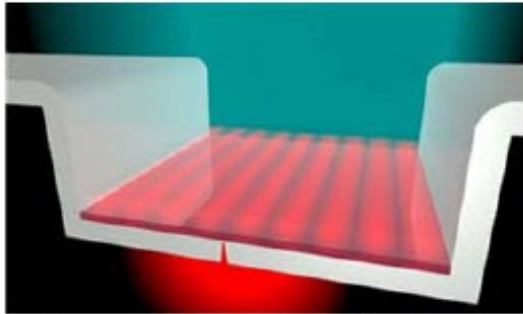
- Single-mode WDM fibers
- New materials; multiple temp zones
- BIST, continuous test while running, intelligent redundancy & self-repair
- WDM mux-demux on chip
- High-volume production and a strong and competitive supply chain

Upcoming challenges/solutions in integrated photonics

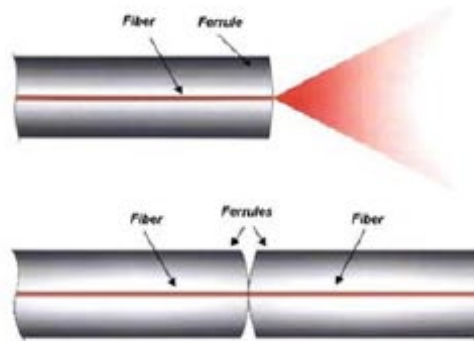


HETEROGENEOUS
INTEGRATION ROADMAP

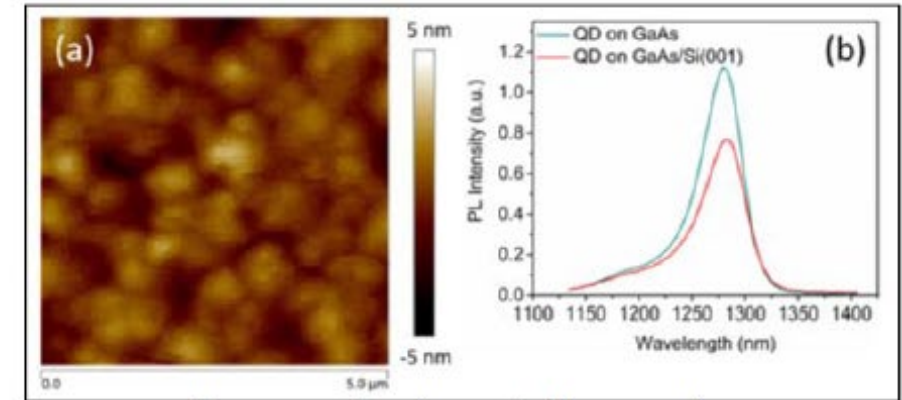
https://eps.ieee.org/images/files/HIR_2019/HIR1_ch09_photonics.pdf



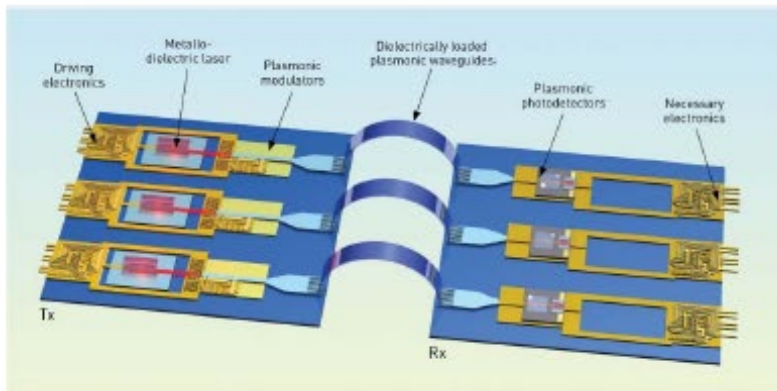
Plasmonic Laser W. Zhu et al.
NIST Science Advances (2017)



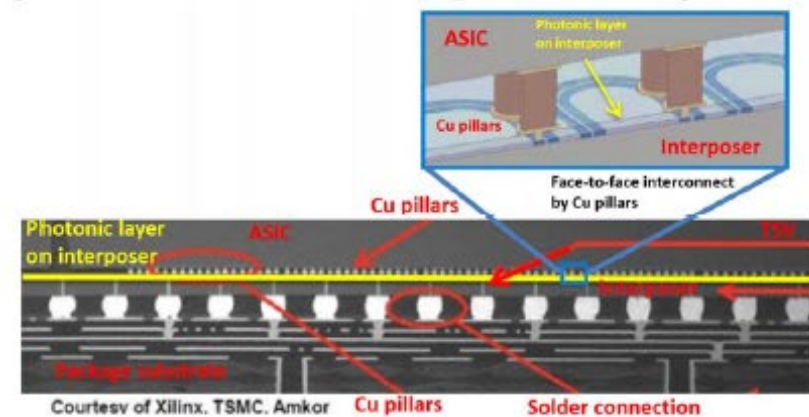
Low-loss Photonic Connectors



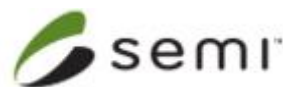
Quantum Dot Laser S. Chen et al.
Vol. 25, No. 5 | 6 Mar 2017 | OPTICS EXPRESS 4632



Plasmonic Communication J. Leuthold et al.
Optics & Photonics News(2013), pp. 28-35.



Electronic/Photonic Interposer



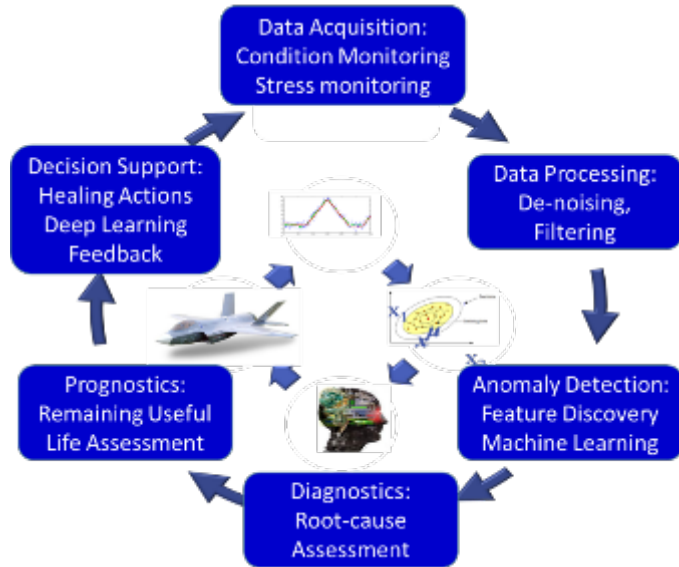
HI System Reliability



HETEROGENEOUS
INTEGRATION ROADMAP

Fusion of bottom-up physics
and top-down AI approaches

Prognostics and Health Management



Machine Learning & Artificial Intelligence

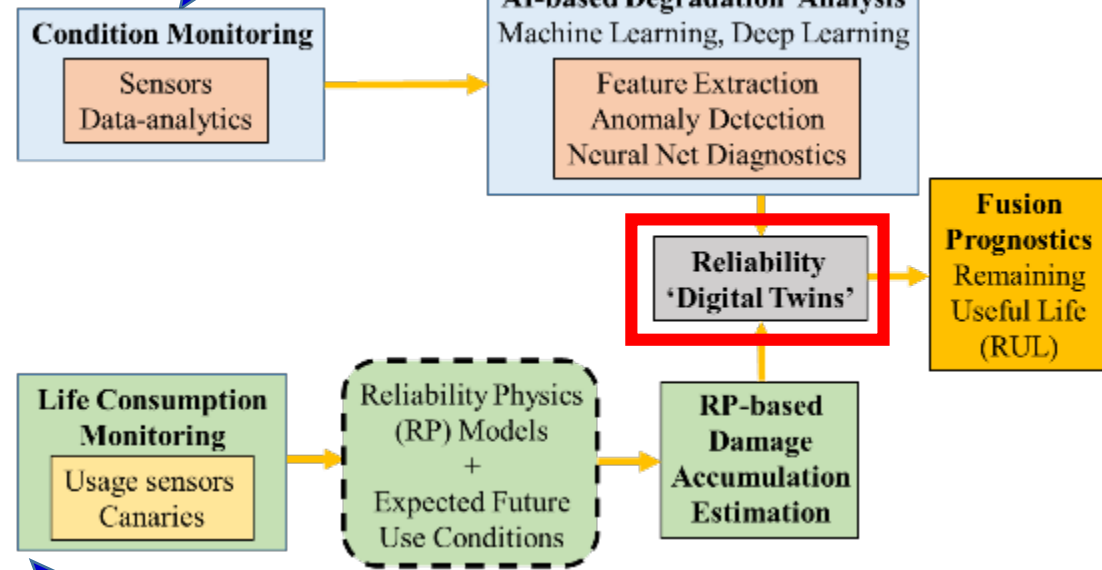
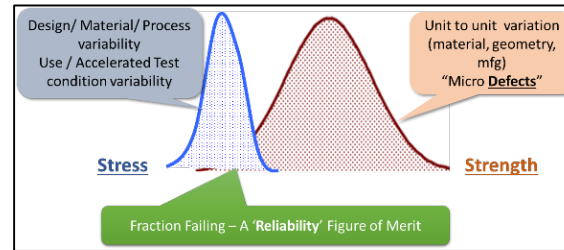
Degradation and Failure Mechanisms

Overstress Mechanisms

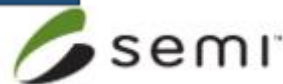
- Mechanical**: Yield, Fracture, Interfacial de-adhesion
- Thermal**: Glass transition (T_g), Phase transition
- Electrical**: Dielectric breakdown, Electrical overstress, Electrostatic discharge, Second breakdown
- Radiation**: Single event upset
- Chemical**: -

Wearout Mechanisms

- Mechanical**: Fatigue, Creep, wear
- Thermal**: Stress driven diffusion voiding (SDDV)
- Electrical**: TDDB, Electromigration, Surface charge spreading, Hot electrons, CFE, Slow trapping
- Radiation**: Radiation embrittlement, Charge trapping in oxides
- Chemical**: Corrosion, ECM, Dendrites & whiskers, Depolymerization, Intermetallic Growth

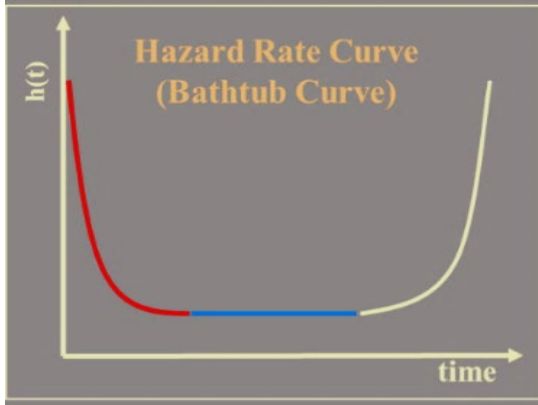


Reliability Physics

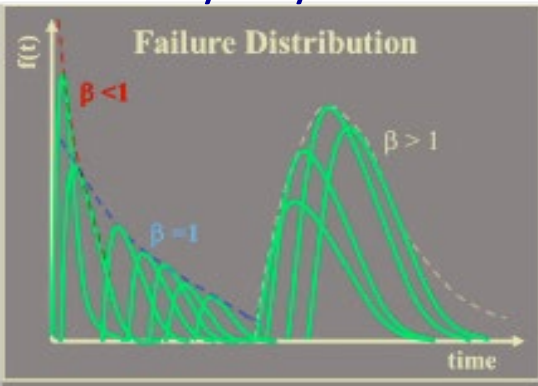


Reliable HI Systems: Approach

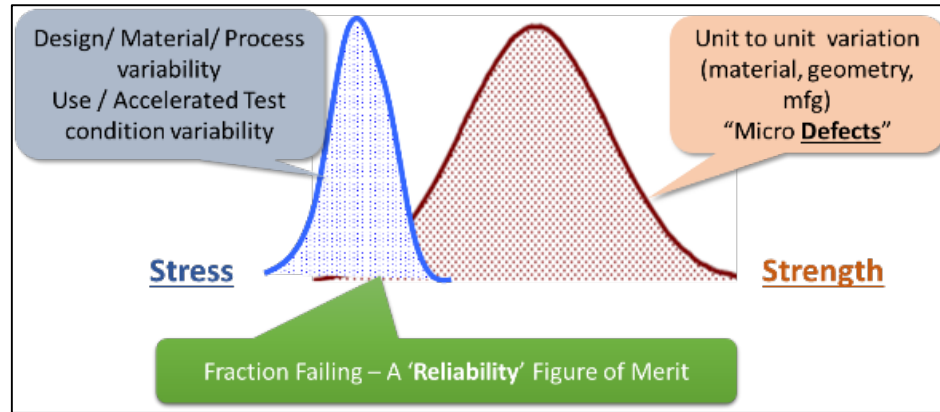
Top down:
Artificial Intelligence
and Machine Learning



Bottom up:
Reliability Physics



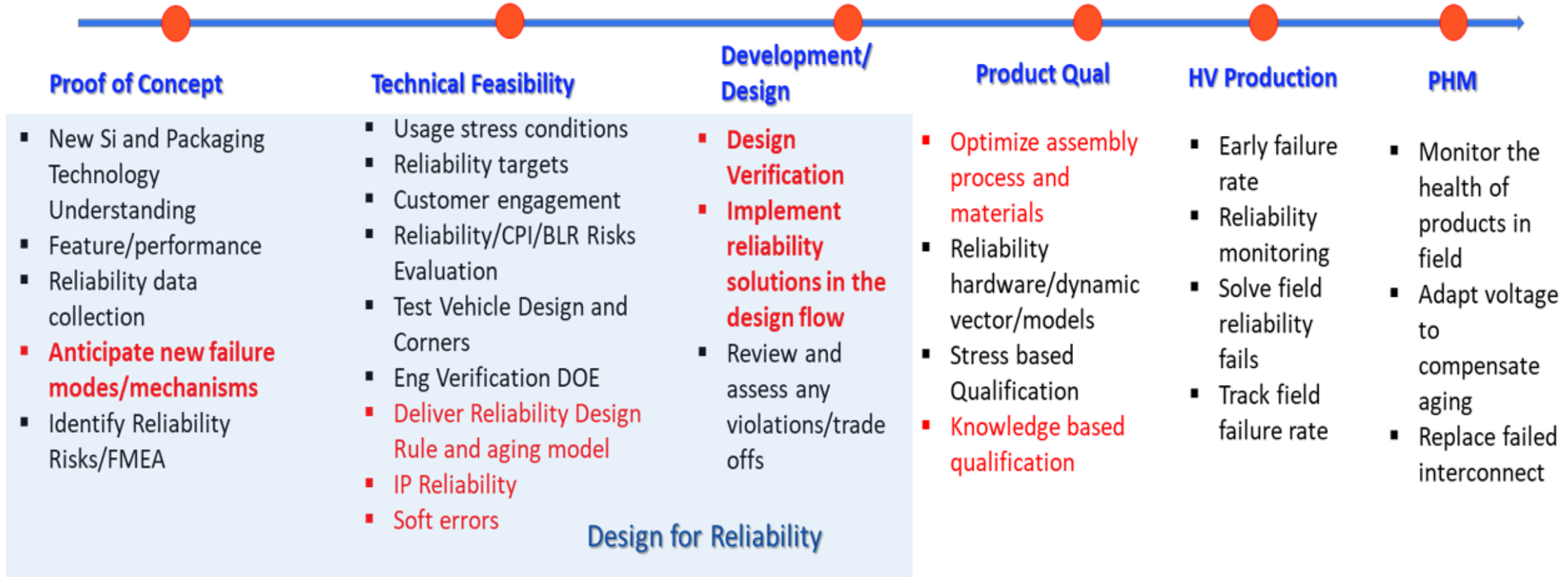
Reliability Assurance Activities



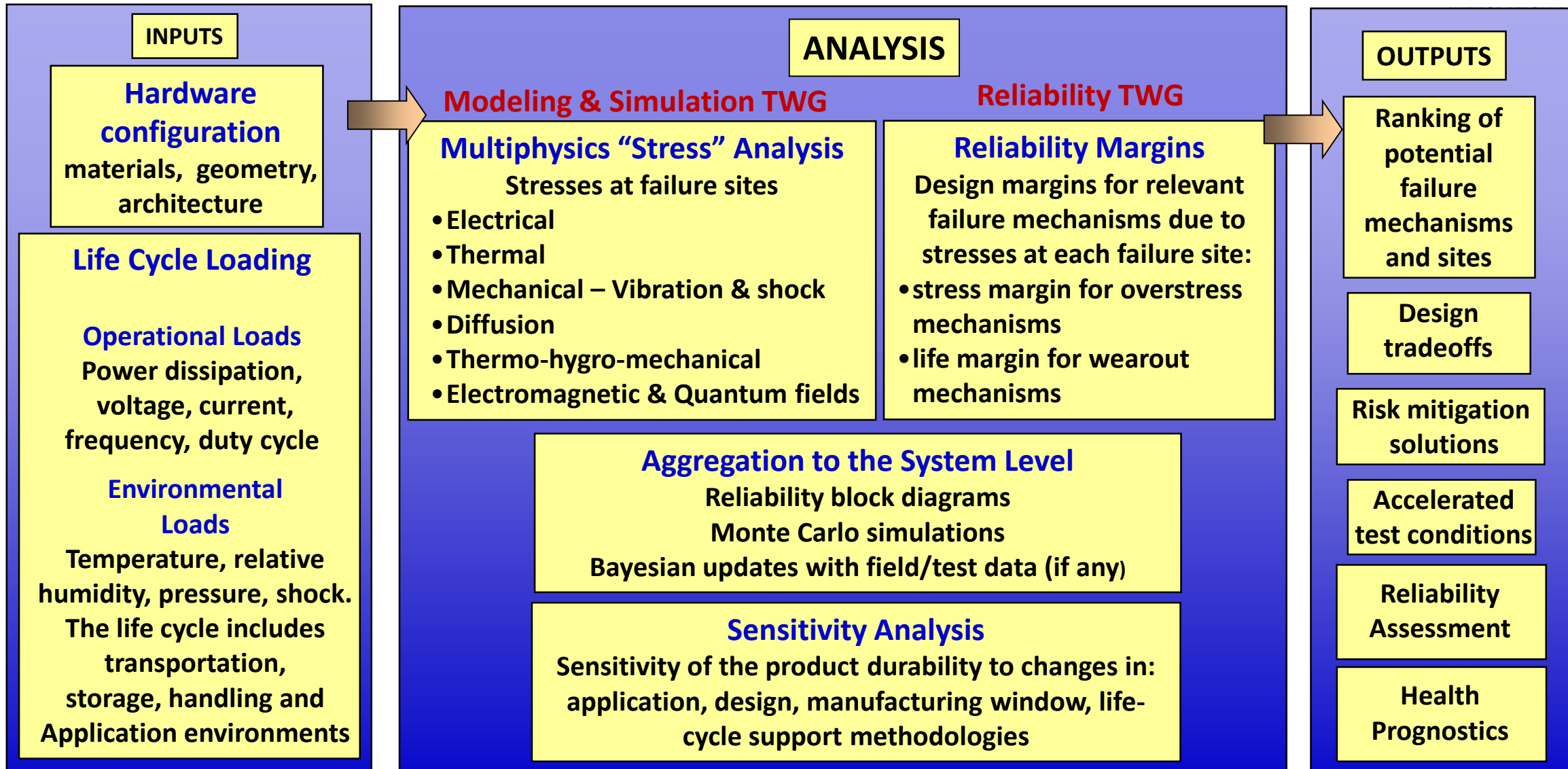
Multi-physics/multi-scale HI systems require holistic cradle-to-grave methodology



Reliability functions in product lifecycle

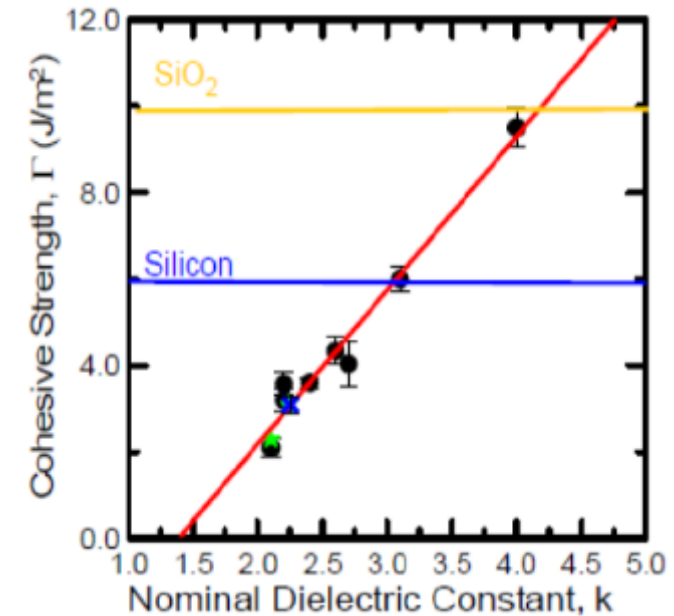
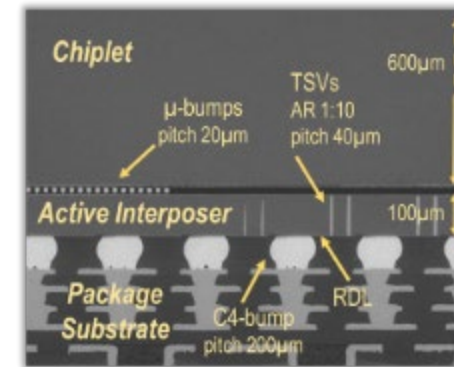
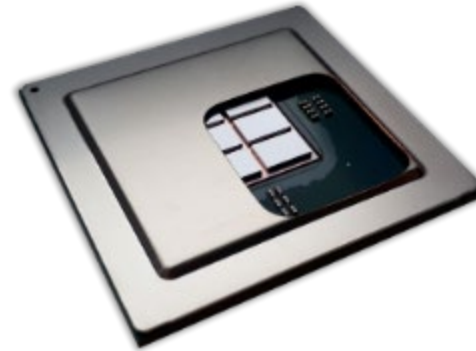
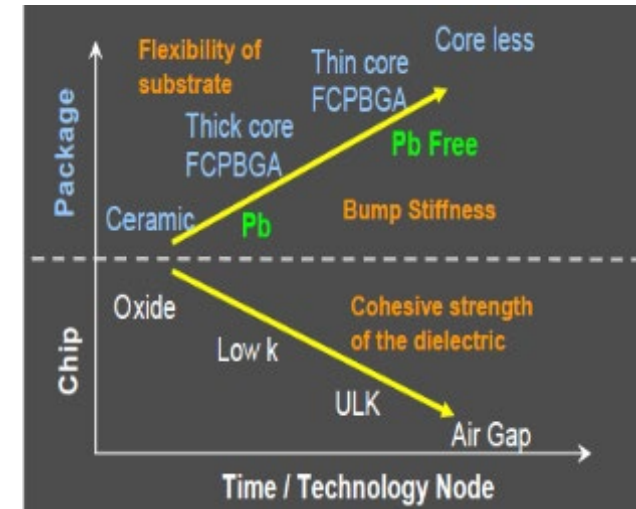


Designing for reliability: Reliability-physics process



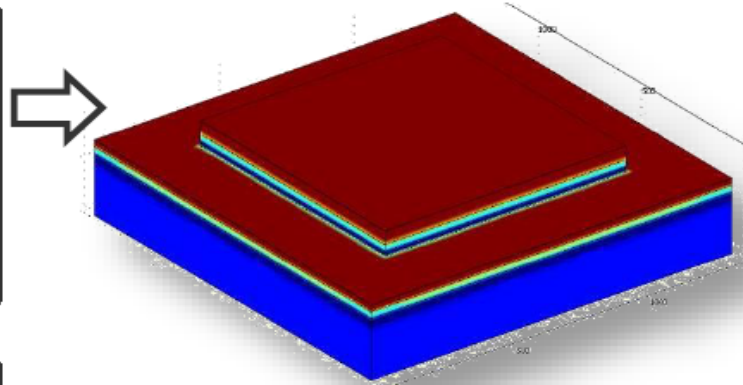
HI systems: CPI challenges

- ❑ CPI issues are increasing with newer Si nodes
 - ❑ Device and packaging reliability were treated separately in old nodes
 - ❑ Advanced Si with low k, CPI requires co-development of device and package
- ❑ Low k and Ultra low k introduction
 - ❑ Fragile and poor adhesion
- ❑ Build up substrate
 - ❑ High CTE and warpage
- ❑ Pb free or Cu pillar interconnect
 - ❑ Higher modulus
- ❑ Complex die
 - ❑ Big die size
 - ❑ Higher power
- ❑ Bump on trace
- ❑ More advanced packaging induced board-chip-package interaction
 - ❑ WLP
 - ❑ 2.5D/3D
 - ❑ Big FCBGA

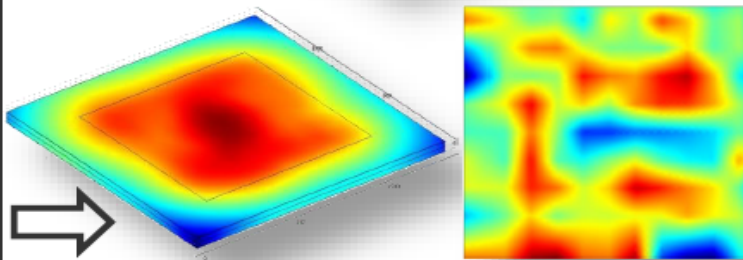


Multi-scale and multi-physics CPI flow

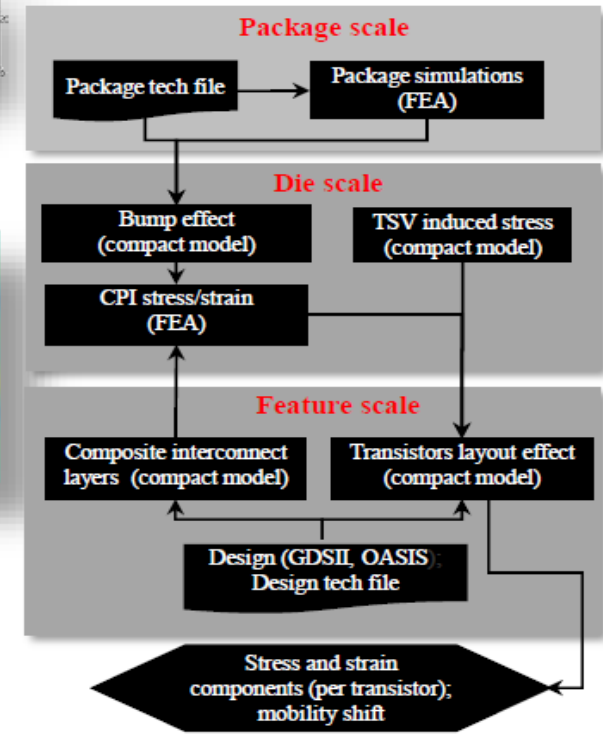
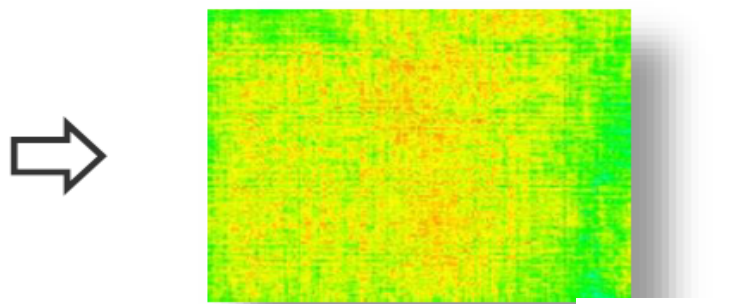
Package-scale simulation (FEA)
Input: geometry; material properties; smeared mechanical properties for RDLs, Silicon/TSV bulk, interconnect.
Output: field of displacement components on the die faces.



Die-scale simulation (FEA)
Input: geometry; field of displacements on the die faces; coordinate-dependent mechanical properties for RDLs, Silicon/TSV bulk, interconnect.
Output: Distribution of the strain components across device layer.

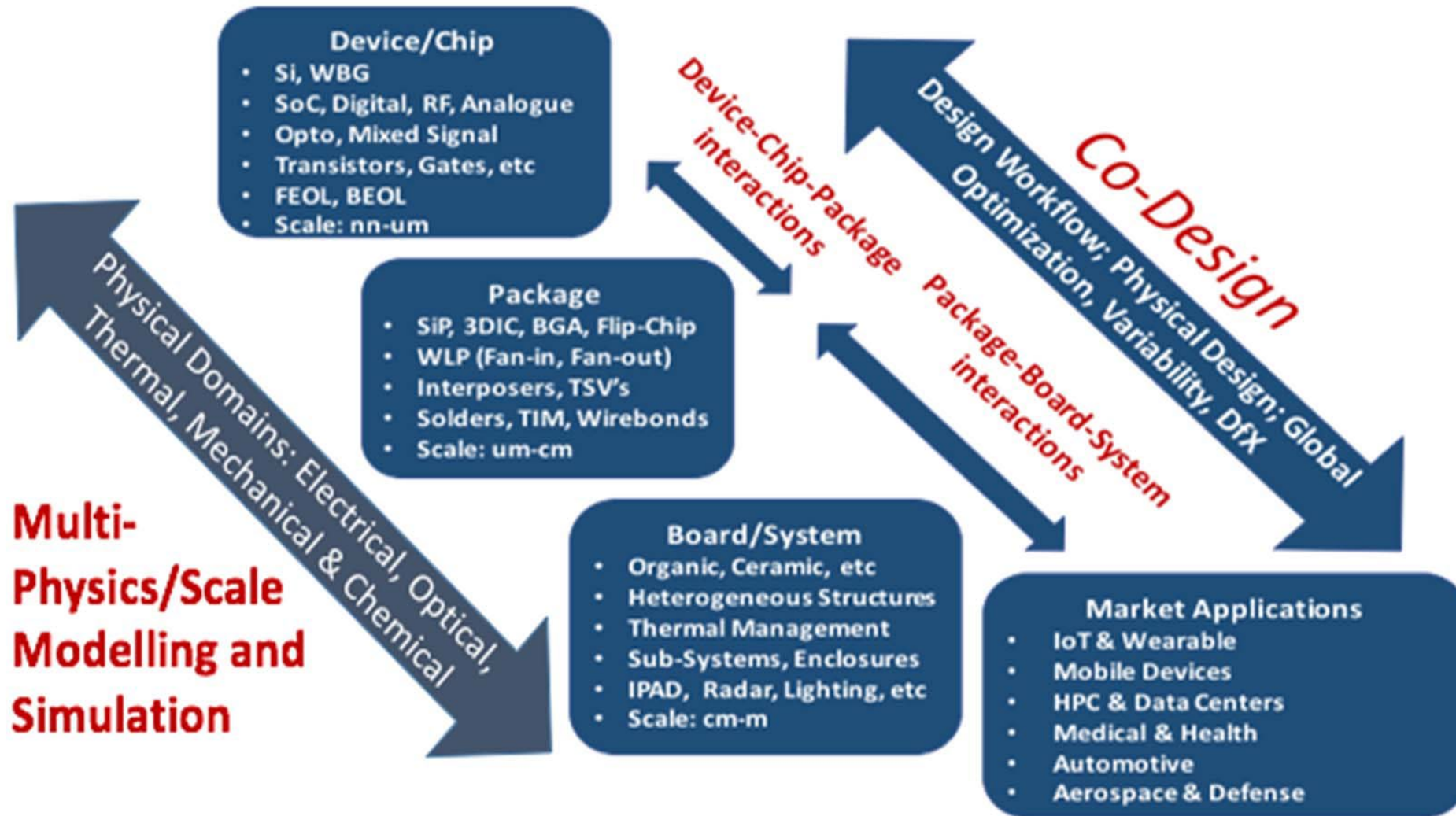


Layout-scale w/feature-scale resolution (compact model):
Input: GDS; distribution of the strain components across device layer.
Output: Transistor-to-transistor variation in stress components



Source: Mentor Graphics

Physics-based modeling simulation and co-design



Source: HIR; Modelling and Simulation TWG

Modes/Mechanisms/Models for degradation & failure



HETEROGENEOUS INTEGRATION ROADMAP

Electrical Thermal Moisture Thermo-mechanical Mechanical DfR Methods MfR Methods

Multiphysics

Devices

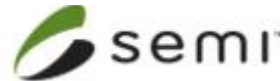
Multiscale

Interconnects

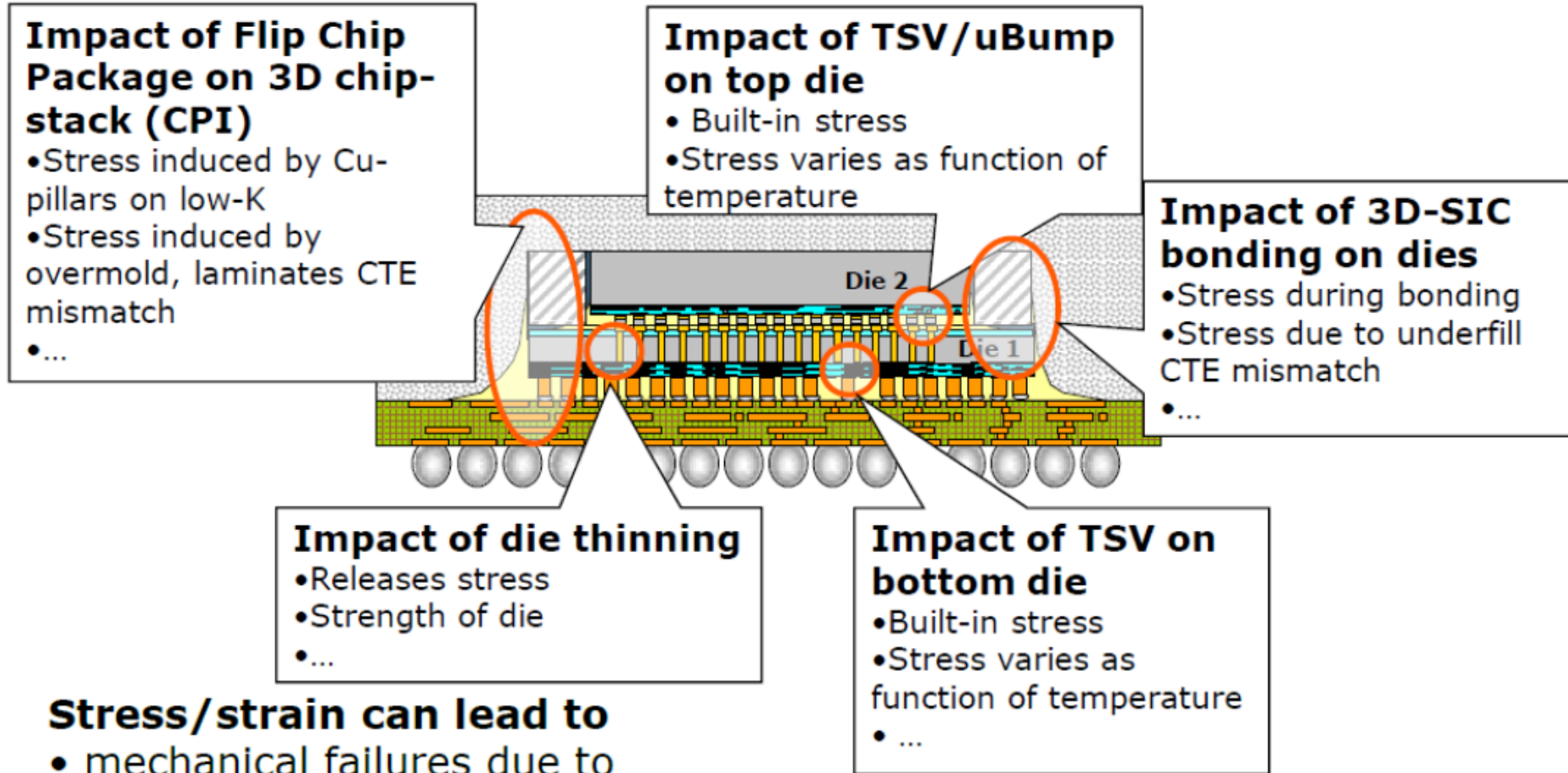
Packaging/ System

Module/System

Multiscale Integration	Multi Physics	Electrical Stress		SI/PI (Electrical Performance)	Thermal Analysis	Moisture		Thermo-Mechanical Stress		Mechanical Stress		Thermal Interaction with SI/PI	Stress Interaction with SI/PI	Simulation/Modeling and Co-Design Flows		Manufacturing Variability	Material Property and Verifiability	
		Failure Modes	Failure Mechanism and Reliability Models			Failure Modes	Failure Mechanism and Reliability Models	Failure Modes	Failure Mechanism and Reliability Models	Failure Modes	Failure Mechanism and Reliability Models			Failure Modes	EDA Flows	PDK/ADK		
Transistor	FinFET and GAA	Leakage current, ripple currents, unlabeled performance and ESD	N/PBTI models with recovery; HCI model; TDDB Weibull model; Oxide & junction breakdown model	Transistor SPICE	FinFET SHE	No known failures	None	FinFET SHE channel stress; μ bump/CA bump/TSV; system level stresses	FinFET SHE Models; CPI Model; Piezo-electrical models	No known failures	None	SHE effect on SPICE parameters	Influence of Si stress on SPICE parameters	Effects of degradation mechanisms and process variabilities on electrical functionality	Cadence; Relapert; Mentor Graphics	Integrate degradation models into Device SPICE Model		
Interconnects	MEOL/BEOL Metal/Via /ILK	Electromigration; Inter Layer Dielectric EIS breakdown; MEOL Dielectric breakdown; ECS	Electromigration model; Dielectric breakdown model	Extraction of RLC Model	Joule Heating simulation; SHE effects on MEOL/BEOL	Pad and underline metal corrosion; Cu/ELK delamination & Cu loss/diffusion	Electrochemical corrosion; Interface degradation due to moisture absorption; Barrier metal oxidation	SHE failure in Cu/ELK, MEOL, BEOL, μ bump, TSV; RDL failures from package stress, Cu fatigue; LowK/ELK layer cracking & delamination	Creep induced voiding; CTE mismatch; SHE induced localized thermal cycling	LowK/ELK layer cracking & delamination	Fatigue by bending	Joule/SHE temp effects on RLC	Effect of Cu/ELK stress on RLC	CPI induced Cu/ELK cracking; SHE/SHE stresses; stress from bumps/TSV/RDL & Packaging	Ansys Mentor			
	BEOL RDL/Dielectric	RDL/UBM Electromigration	Electromigration	Extraction of RDL RLC Model	BEOL Joule/SHE effect on RDL temperature	Cu dendrite	Electro-chemical corrosion	RDL cracking	μ bump/TSV/ Package/ Board effects on RDL stress			Effect of RDL temp on electrical model	Effect of RDL stress on electrical model	CPI/CBI induced failures; RDL cracking & delamination	Effect of temp and stress on RDL EM			
	Au/Cu Wirebonding	Electromigration				WMC Corrosion		Bond wire fatigue		Cu/ELK cracking	Bonding force models							
	μ Bump/CA Bump/UBM	Electromigration induced voids	Black's model; Multiphysics EM mode including electron, thermal gradient, stress gradient and atomic diffusion	μ bump electrical model	Die Internal Joule/SHE temp effect & external temp effect on bump temperature	SBM delamination	Galvanic effect (electro-chemical reaction)	Bump joint cracking; Under bump ELK cracking; Under pad cracking in substrate	CTE mismatch induced stress; Fatigue		Tensile stress causes bump peel; cracks at μ bump; UBM and interface	Fracture/fatigue from shock, drop, impact, Vbr; e.g. in die attach, dielectric layer, interposer, UBM, solder joints	Effect of temp on bump electrical model	Effect of bump stress on electrical model	Multi Physics Bump EM - local current, temp, temp gradient and stress effect on μ bump EM	Bump fatigue; effect of local temp & stress on fatigue life		
TSV/Interposer/EMIB	Electromigration; Barrier Dielectric breakdown	Black's model; Multiphysics EM mode including electron, thermal gradient, stress gradient and atomic diffusion	TSV electrical model	Internal Joule/SHE temp effect on the TSV temp; External temp effect on TSV temp.			Cu pumping/TSV pop up	Cu extrusion due to CTE mismatch with Si; plastic ratcheting at high temp				Effect of TSV temp on electrical model	Effect of TSV stress on electrical model	TSV EM response to local current, temp field and stress; TSV Pop out and effects on TSV/TSV delamination	Barrier breakdown - flow does voltage/current, temp and stress effect TSV barrier BDF	Package material thermal/mechanical properties; Die metal stack and thermal/mech properties; μ bump/TSV thermal mechanical		
Packaging/ System	Passivation	Passivation cracking	ECS induced cracking			Passivation cracking & delamination; underfill/Mold compound delamination		Passivation cracking										
	Underfill					Underfill to die/substrate delamination; underfill swelling	Moisture degradation in underfill & at interfaces	Bump joint cracking	Solder joint fracture and fatigue due to underfill expansion									
	High Density Substrate	Metal trace electromigration		Package Substrate RLC model extraction	Co-thermal sim from die to package	Metal trace corrosion		Metal trace/via cracking				Thermal - electrical performance interactions	Mechanical - electrical performance interactions	Cu trace EM - effect of local current, temp and stress	Thermal & mechanical effect on Cu trace/via cracking			
	Wafer Level Package Fanout Package 2.x/2.5D Interposer Package (Cu/WoS and EMIB, etc)								Warpage									
	3D Package (Foveros, etc)				Mold compound pop-corn; Anisotropic conductive adhesive cracks				FinFET ion shift (due to TSV/Si CTE mismatch, μ bump stress, shrinkage of underfill & EMC); TSV effects on BTI/HCI; BEOL cracking; Cu pillar joint failure; Mold compound pop-corn; conductive adhesive cracking									
	Chiplet/RGD	ESD							Die edge cracking; Under bump ELK cracking									
Module/ System	Printed Circuit Board Assembly	Leakage current and shorts from Conductive filament formation	electro-chemical metal migration	PCB board electrical model	Co-thermal sim from die to package to system	Leakage current and shorts from loss of surface insulation resistance & conductive filament formation	moisture ingress, leading to fiber-matrix debonding and electro-chemical metal migration	Solder joint cracking; Cracking of PTH plating; PCB delamination; trace cracking; Warpage	thermo-mechanical fatigue of trace and solder; IMC fracture; CTE mismatches between component / PWB, metallization/ dielectrics	Solder joint cracking; pad cratering	Stress exceeds the material and interface strength	Effects of PCB temp and corrosion on electrical model?	Effects of PCB stress on electrical model?	Board level Solder joint Reliability	ANSYS Mechanical	PCB thermal/ mechanical properties; Solder joint fatigue/creep model; Solder joint dynamic properties		



HI Packaging: An overview of 3D IC stresses and reliability



Stress/strain can lead to

- mechanical failures due to delamination, peel, fatigue, ...
- electrical impact due to parameter shifts, increased variability, EM,...

Multi-scale

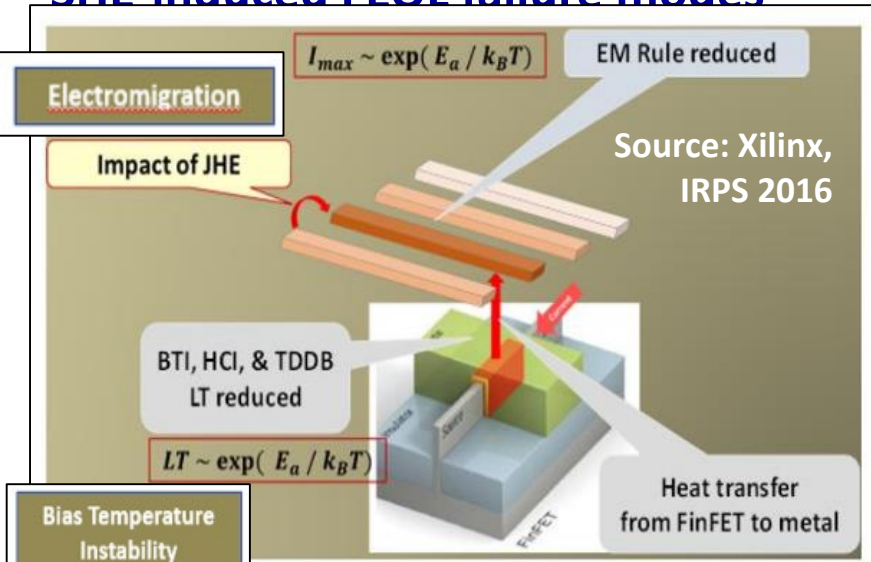
Source: IMEC

CBPI-induced degradation and failure modes

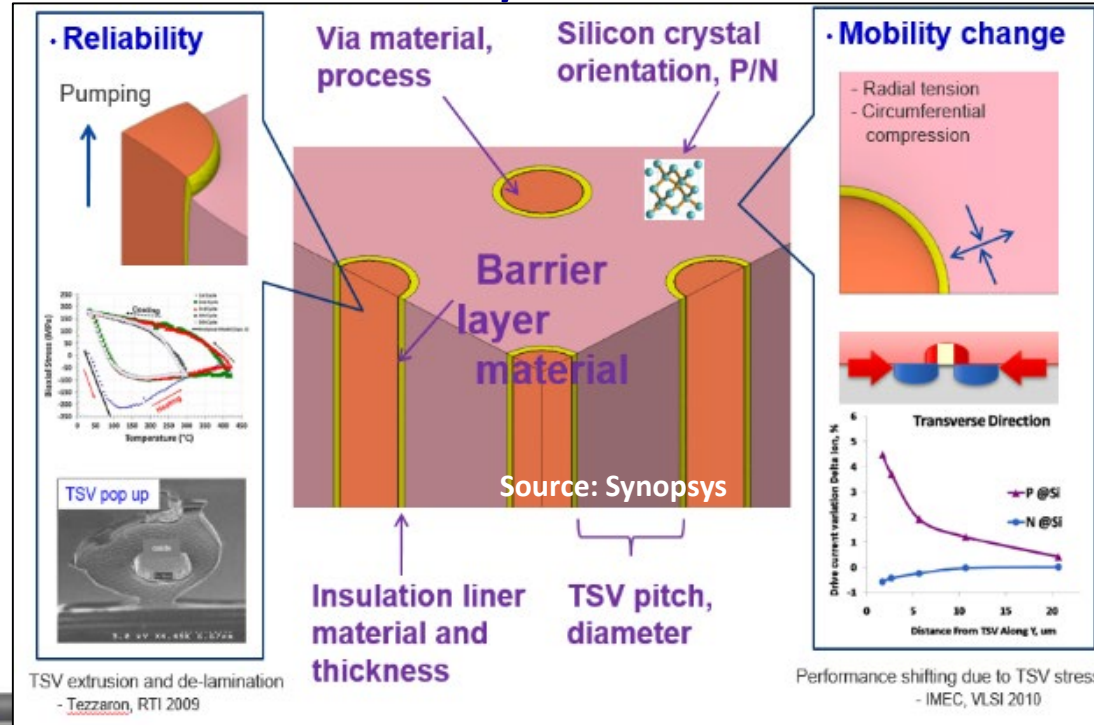


HETEROGENEOUS INTEGRATION ROADMAP

SHE-induced FEOL failure modes

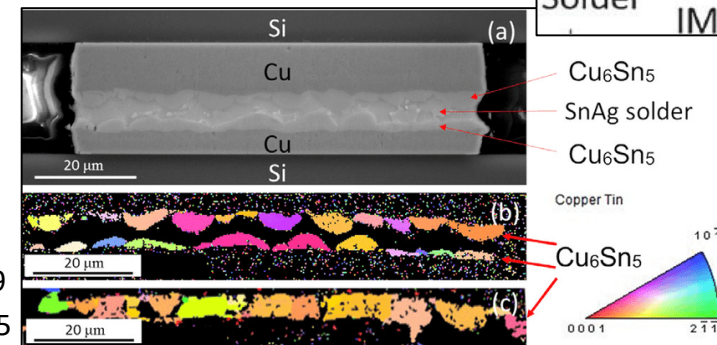
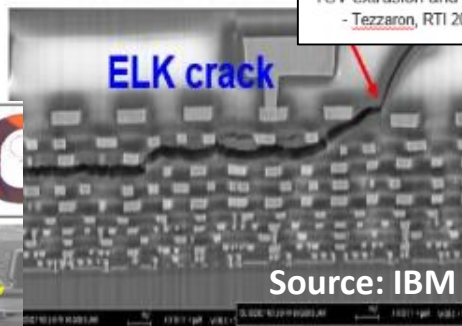
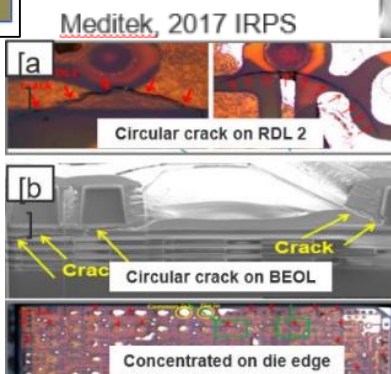
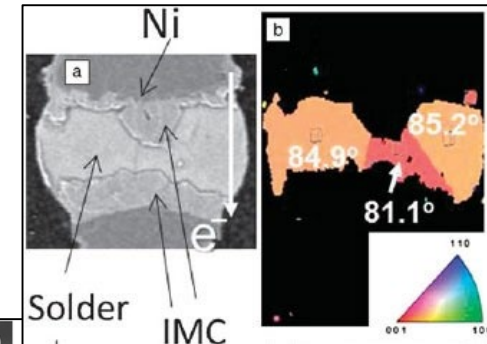


CPI-induced MEOL/BEOL failure modes



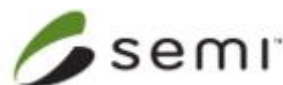
Microbumps:

- Material anisotropy
- Length-scale effects



DOI.org/10.1557/mrs.2015.29

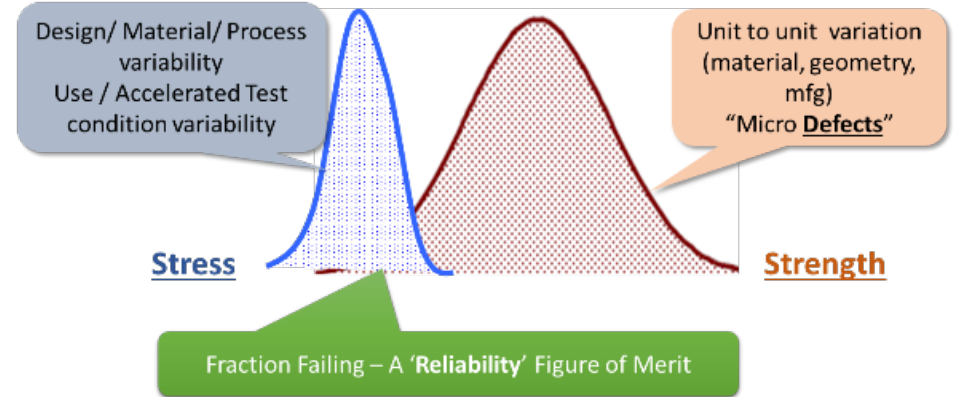
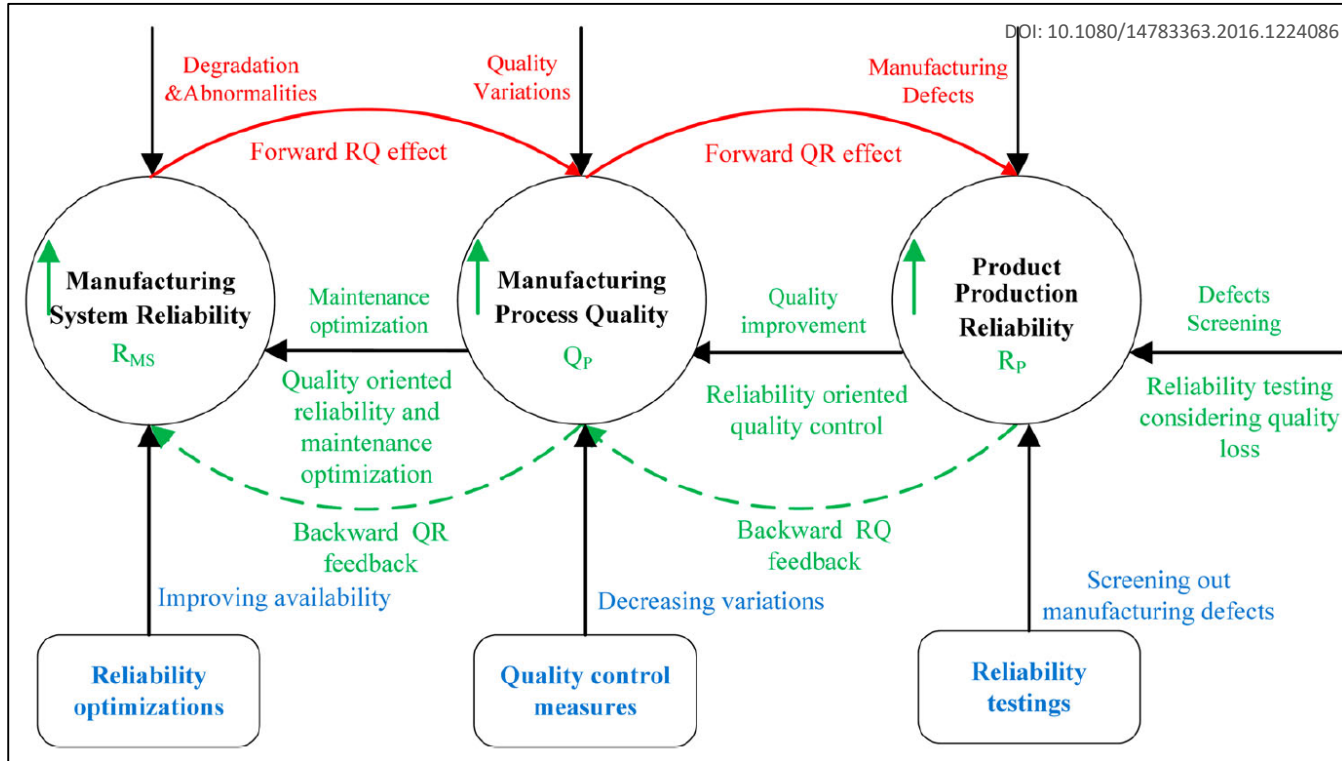
DOI:10.1016/j.scriptamat.2020.01.005



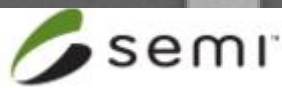
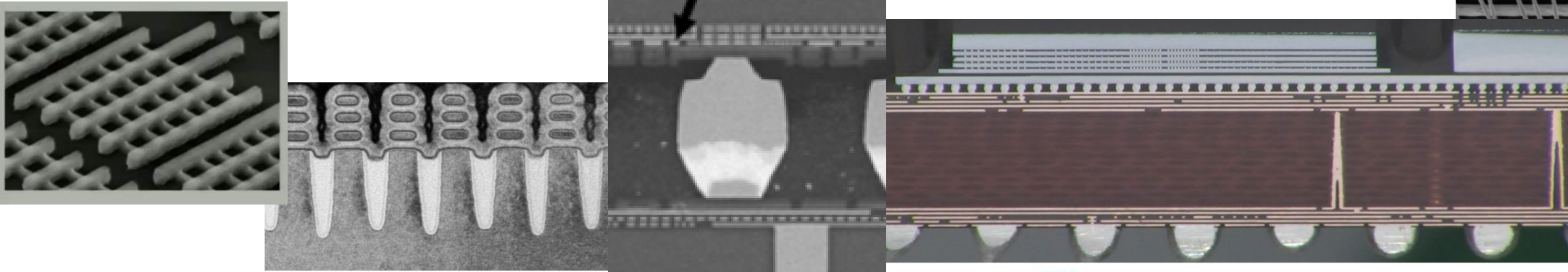
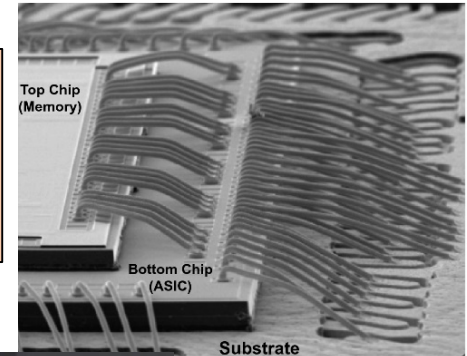
Influence of manufacturing quality on reliability



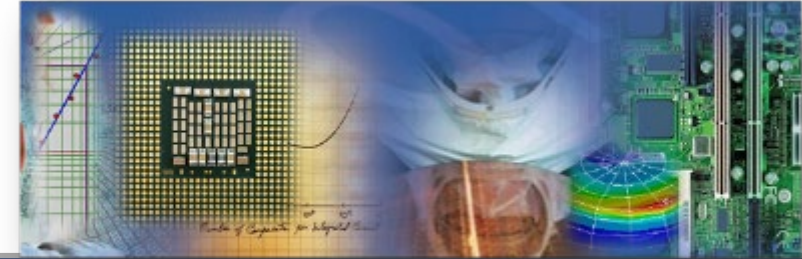
HETEROGENEOUS INTEGRATION ROADMAP



Process metrology poses significant challenge for HI Systems

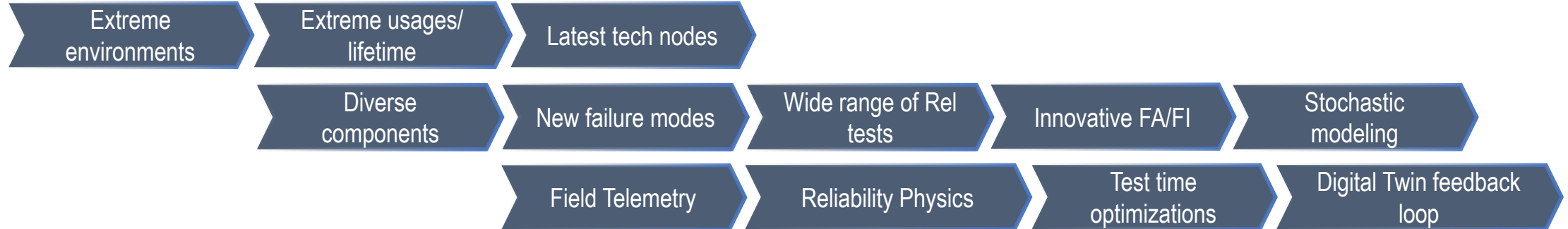


Qualification and testing: Reliability validation/verification



The changing and challenging landscape

Need for dynamic, flexible models and methods



Multi-physics methods to quantify 'stress' and 'strength' distributions at potential sites of failure

Qualification testing needs to be Customized, Knowledge-based and Innovative

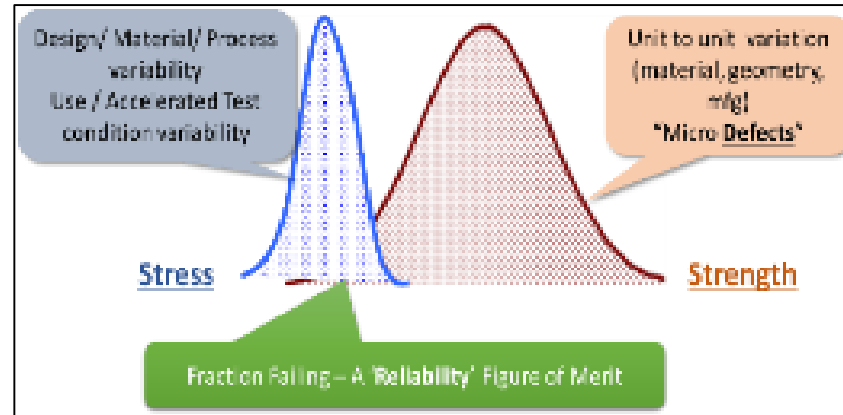
Data feedback loop with Digital Twins to validate failure characteristics and run virtual experiments

Integrated PHM - Self-cognizant, intelligent, bio-mimetic hardware to 'age with grace'

Reliability Challenges: Future Outlook

		Reliability Targets	Life Cycle Conditions	Design for Reliability	Manufacturing for Reliability	Qualification for Reliability	Sustainment for Reliability	Supply Chain
Applications	Mobile	<p>1-5 Years:</p> <p>Multi-physics fusion approaches for reliability assurance</p> <ul style="list-style-type: none"> • Bottom-up <i>Reliability Physics</i> based approaches, tools, infrastructure • Top-down <i>Machine Learning & AI</i> based approaches, tools, infrastructure <p>5-10 Years:</p> <p>Fusion approaches for co-design (based on 'digital twins') and life-cycle PHM of next-gen robust HI systems</p> <ul style="list-style-type: none"> • Fault-tolerant systems • Resilient systems <p>10-15 Years:</p> <p>Fusion approaches for intelligent, adaptive, reconfigurable products with integrated autonomous life-cycle management capability</p> <ul style="list-style-type: none"> • Intelligent, self-cognizant systems • Self-healing systems 						
	IoT							
	Medical, Health and wearables							
	Automotive							
	HPC & Data Centers							
Aerospace and Defense								
Package Integration	WLP (FO/FI)							
	2.5D and 3D integration							
	Wafer Singulation and Thinning							
	Chip-package interactions (CPI)							
	Interconnects (TSV8s, μ bumps, wirebonds, Flip Chip solder joints)							
	Substrates/Interposers							
	Board Assembly							
SOC/SIP/SOP ⁹ formats								
Technologies	Microelectronics > 10 nm							
	Microelectronics <10 nm							
	Photonics & optics							
	MEMS and sensors							
	Power electronics							
	Energy sources (Batteries/PV ⁶ /FC ⁷)							
	RF/Analog Devices							

Reliability assurance activities



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